NEC
ELECTRON DEVICE

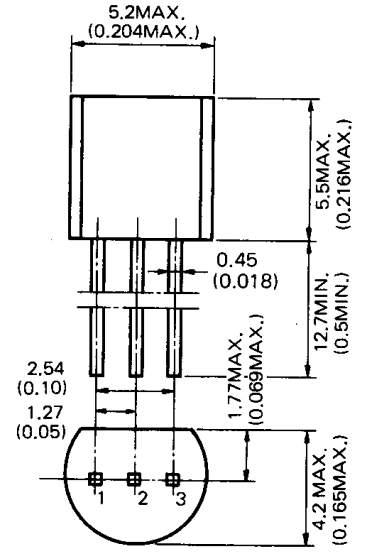
NPN SILICON TRANSISTOR
2SC2407

DESCRIPTION The 2SC2407 is designed for UHF and VHF amplifier.

FEATURES

- P_{out}: 160 mW TYP. @ f=500 MHz, V_{CC}=12.6 V
  P_i=5 mW (Class B)

PACKAGE DIMENSIONS
in millimeters (inches)



1. BASE
2. EMITTER
3. COLLECTOR

EIAJ : SC-43A
JEDEC: TO-92
IEC : PA33

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures

- Storage Temperature . . . . . −65 to +150 °C
- Junction Temperature . . . . . +150 °C Maximum

Maximum Power Dissipation (Ta=25 °C)

- Total Power Dissipation . . . . . 600 mW

Maximum Voltages and Currents (Ta=25 °C)

- V_{CBO} Collector to Base Voltage . . . . . 35 V
- V_{CEO} Collector to Emitter Voltage . . . . . 18 V
- V_{EBO} Emitter to Base Voltage . . . . . 3.0 V
- I_C Collector Current . . . . . 150 mA
- I_B Base Current . . . . . 50 mA

ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
h_{FE}	DC Current Gain	20	60	200		V_{CE}=10 V, I_C=50 mA
C_{ob}	Output Capacitance		1.0	2.0	pF	V_{CB}=10 V, I_E=0, f=1.0 MHz
P_{out}	Output Power	20	22		dBm	V_{CC}=12.6 V, P_{in}=7 dBm, f=500 MHz (Class B)
I_{CBO}	Collector Cutoff Current			0.5	μA	V_{CB}=20 V, I_E=0
I_{EBO}	Emitter Cutoff Current			0.5	μA	V_{EB}=2.0 V, I_C=0